

ABSTRACT

Densely disposed patterns constituting a semiconductor integrated circuit device are divided into a first mask pattern and a second mask pattern 28B such that a phase shifter S can be disposed, and a predetermined pattern is transferred on a semiconductor substrate by multiple-exposure thereof. The second mask pattern 28B has a main light transferring pattern 26c1, a plurality of auxiliary light transferring patterns 26c2 disposed thereabout, and a phase shifter S disposed in the main light transferring pattern 26c1. The auxiliary light transferring patterns 26c2 are disposed such that respective distances from a center of each thereof to a center of the main light transferring pattern 26c1 are substantially equal. With this arrangement, a densely disposed pattern is transferred with sufficient process transfer margin.

(Selected drawing; Fig. 32)